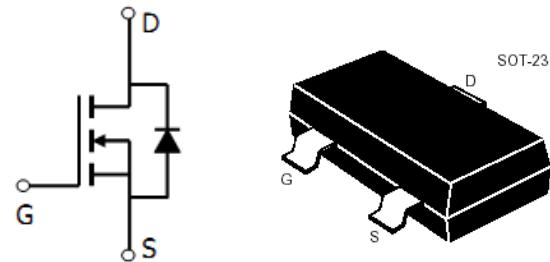


GM3400

SOT-23 場效應晶體管(SOT-23 Field Effect Transistors)



N-Channel Enhancement-Mode MOS FETs

N 沟道增强型 MOS 场效应管

■MAXIMUM RATINGS 最大額定值

Characteristic 特性參數	Symbol 符號	Max 最大值	Unit 單位
Drain-Source Voltage 漏極-源極電壓	BV_{DSS}	30	V
Gate- Source Voltage 柵極-源極電壓	V_{GS}	± 12	V
Drain Current (continuous) 漏極電流-連續	I_D	5	A
Drain Current (pulsed) 漏極電流-脉冲	I_{DM}	18	A
Total Device Dissipation 總耗散功率 $T_A=25^\circ\text{C}$ 環境溫度為 25°C	P_D	1400	mW
Junction 結溫	T_J	150	$^\circ\text{C}$
Storage Temperature 儲存溫度	T_{stg}	-55 to +150	$^\circ\text{C}$

■DEVICE MARKING 打標

GM3400=B00



东莞市宇芯电子有限公司

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GM3400

GM3400

ELECTRICAL CHARACTERISTICS 電特性(T_A=25°C unless otherwise noted 如無特殊說明，溫度為 25°C)

Characteristic 特性參數	Symbol 符號	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Drain-Source Breakdown Voltage 漏極-源極擊穿電壓(I _D = 250uA, V _{GS} =0V)	BVDSS	30	—	—	V
Gate Threshold Voltage 柵極開啓電壓(I _D = 250uA, V _{GS} = V _{DS})	V _{GS(th)}	0.6	—	2	V
Diode Forward Voltage Drop 內附二極管正向壓降(I _S = 1.25A, V _{GS} =0V)	V _{SD}	—	0.7	1	V
Zero Gate Voltage Drain Current 零柵壓漏極電流(V _{GS} =0V, V _{DS} = 30V)	I _{DSS}	—	—	1	uA
Gate Body Leakage 柵極漏電流(V _{GS} =±12V, V _{DS} =0V)	I _{GSS}	—	—	±100	nA
Static Drain-Source On-State Resistance 静态漏源導通電阻(I _D = 5A, V _{GS} =10V)	R _{DS(ON)}	—	35	41	mΩ
Static Drain-Source On-State Resistance 静态漏源導通電阻(I _D = 3.5A, V _{GS} =4.5V)	R _{DS(ON)}	—	40	45	mΩ
Static Drain-Source On-State Resistance 静态漏源導通電阻(I _D = 3A, V _{GS} =2.5V)	R _{DS(ON)}	—	50	55	mΩ
Input Capacitance 輸入電容 (V _{GS} =0V, V _{DS} = 15V, f=1MHz)	C _{ISS}	—	545	—	pF
Output Capacitance 輸出電容 (V _{GS} =0V, V _{DS} = 15V, f=1MHz)	C _{OSS}	—	66	—	pF
Turn-ON Time 开启時間 (V _{DS} = 15V, V _{GS} = 10V, R _{GEN} =6Ω)	t _(on)	—	9.6	—	ns
Turn-OFF Time 关斷時間 (V _{DS} = 15V, V _{GS} = 10V, R _{GEN} =6Ω)	t _(off)	—	39	—	ns

Pulse Width≤300 μ s; Duty Cycle≤2.0%